

rotating the polishing cloth along a central axis thereof and pressing the tool on a radial portion of the polishing cloth, said tool being moved along [a radial direction of] the polishing cloth [and perpendicular to the radial direction] to thereby form the fluff on the polishing cloth so that the polishing cloth can evenly and continuously polish the semiconductor device.

*Rewrite claim 6 as follows:*

6. (Amended) A flattening method of a semiconductor device by a chemical-mechanical polishing process comprising,

preparing a synthetic resin polishing cloth in a circular form and a tool for forming a surface layer of the synthetic resin polishing cloth to have fluff thereon, said tool having an annular shape with a diameter less than a radial length of the polishing cloth,

rotating the polishing cloth along a central axis thereof and pressing the tool on one radial portion of the polishing cloth, said tool being moved along [a radial direction of] the polishing cloth [and perpendicular to the radial direction] to thereby form the fluff on the polishing cloth, and

rotating means for supporting the semiconductor device along a central axis thereof and pressing the semiconductor device on a different radial portion of the polishing cloth to polish the semiconductor device while the tool is moved on the polishing cloth to recreate a surface shape thereof so that the polishing cloth can evenly and continuously polish the semiconductor device.

*Rewrite claim 11 as follows:*

11. (Amended) A flattening apparatus of a semiconductor device by a chemical-mechanical polishing process comprising,

a flattening device having a circular polishing cloth for polishing the semiconductor device, said flattening device being rotated in one direction along a central axis thereof,

a device for forming a surface layer of the polishing cloth having fluff thereon, said